Features

- Compatible with all I²C bidirectional data transfer • protocol
 - Memory array:
 - 32 Kbits (4Kbytes) of EEPROM
 - Page size: 32 bytes
- Single supply voltage and high speed:
 - 1.7V-5.5V/400kHz
 - 2.5V-5.5V/1MHz

Random and sequential Read modes

- Write:
 - Byte Write within 3 ms
 - Page Write within 3 ms

- Partial Page Writes Allowed
- Write Protect Pin for Hardware Data Protection

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- Schmitt Trigger, Filtered Inputs for Noise Suppression
- High-reliability
 - Endurance: 1 Million Write Cycles - Data Retention: 100 Years
- Enhanced ESD/Latch-up protection - HBM 5000V

voltage operation are essential.

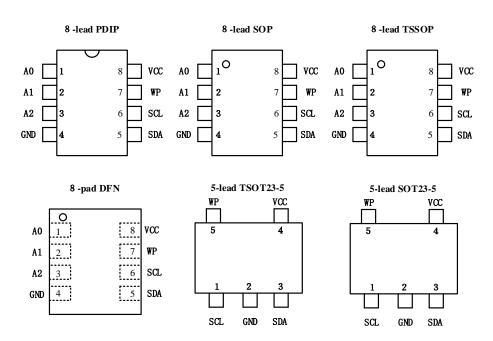
8-lead PDIP/SOP/TSSOP/UDFN and TSOT23-5 packages

commercial applications where low-power and low-

Description

• The BL24C32F provides 32768 bits of serial • The device is optimized for use in many industrial and electrically erasable and programmable read-only memory (EEPROM), organized as 4096 bytes.

Pin Configuration





Pin Descriptions

Pin Name	Туре	Functions
A0-A2	I	Address Inputs
SDA	I/O	Serial Data
SCL	I	Serial Clock Input
WP	I	Write Protect
GND	Р	Ground
Vcc	Р	Power Supply

Table 1

Block Diagram

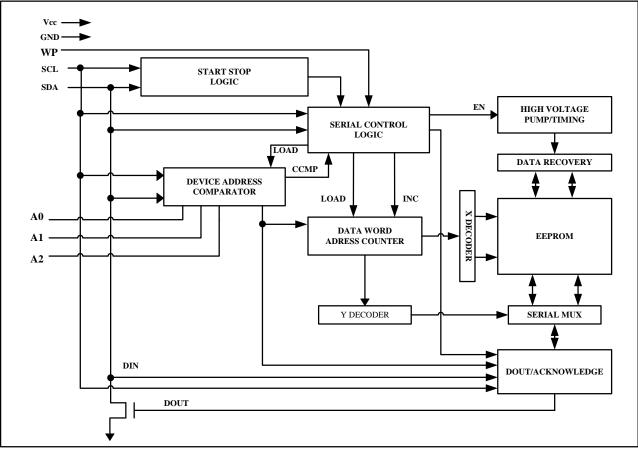


Figure 1

DEVICE/PAGE ADDRESSES (A2, A1 and A0): The A2, A1 and A0 pins are device address inputs that are hard wire for the BL24C32F. Eight 32K devices may be addressed on a single bus system (device addressing is discussed in detail under the Device Addressing section).

SERIAL DATA (SDA): The SDA pin is bi-directional for serial data transfer. This pin is open-drain driven and may be wire-OR'ed with any number of other open-drain or open- collector devices.

SERIAL CLOCK (SCL): The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

WRITE PROTECT (WP): The BL24C32F has a Write Protect pin that provides hardware data protection. The Write Protect pin allows normal read/write operations when connected to ground (GND). When the Write Protection pin is connected to V_{cc} , the write protection feature is enabled and operates as shown in the following **Table 2**.

WP Pin Status	BL24C32F
At VCC	Full(32K)Array
At GND	Normal Read/Write Operations

Table 2

Functional Description

1. Memory Organization

BL24C32F, 32K SERIAL EEPROM: Internally organized with 128 pages of 32 bytes each, the 32K requires a 12-bit data word address for random word addressing.

2. Device Operation

CLOCK and DATA TRANSITIONS: The SDA pin is normally pulled high with an external device. Data on the SDA pin can change only during SCL low time periods (see **Figure 2**). Data changes during SCL high periods will indicate a start or stop condition as defined below.

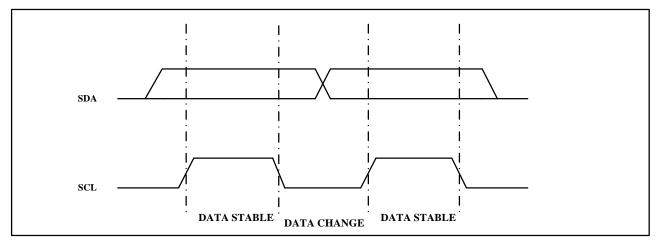


Figure 2. Data Validity



START CONDITION: A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (see **Figure 3**).

STOP CONDITION: A low-to-high transition of SDA with SCL high is a stop condition. (see **Figure 3**).

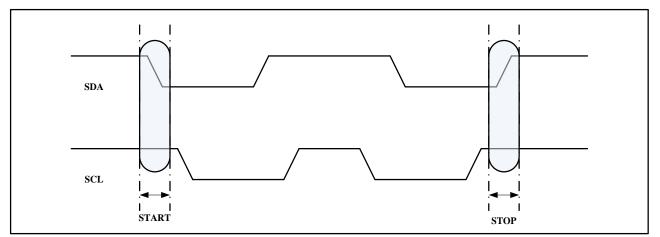


Figure 3. Start and Stop Definition

ACKNOWLEDGE: All addresses and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a "0" to acknowledge that it has received each word. This happens during the ninth clock cycle.

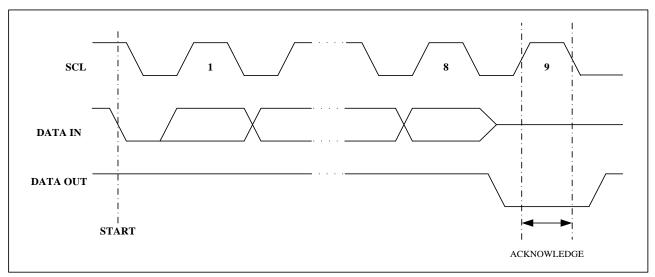


Figure 4. Output Acknowledge

STANDBY MODE: The BL24C32F features a low-power standby mode which is enabled:

(a) upon power-up

(b) after the receipt of the STOP bit and the completion of any internal operations.

MEMORY RESET: After the protocol is interrupted, power loss or system reset, any two-wire part can be reset by following these steps:

- 1. Clock up to 9 cycles.
- 2. Look for SDA high in each cycle while SCL is high.
- 3. Create a start condition.

3. Device Addressing

The 32K EEPROM devices all require an 8-bit device address word following a start condition to enable the chip for a read or write operation (see **Figure 5**)

MSB							LSB
1	0	1	0	A2	A1	A0	R/W

Figure 5. Device Address

The device address word consists of a mandatory "1", "0" sequence for the first four most significant bits as shown. This is common to all the Serial EEPROM devices.

The 32K EEPROM uses A2, A1 and A0 device address bits to allow as much as eight devices on the same bus. These 3 bits must be compared to their corresponding hardwired input pins. The A2, A1 and A0 pins use an internal proprietary circuit that biases them to a logic low condition if the pins are allowed to float.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a "0". If a compare is not made, the chip will return to standby state.

DATA SECURITY: The BL24C32F has a hardware data protection scheme that allows the user to write protect the entire memory when the WP pin is at VCC.

4. Write Operations

BYTE WRITE: A write operation requires two 8-bit data word address (see **Table 3 & Table 4**) following the device address word and acknowledgment. Upon receipt of every 8-bit address, the EEPROM will respond with a "0" and then send 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a "0" and the master device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally timed write cycle, tWR, in order to save the data in the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (see **Figure 6**).

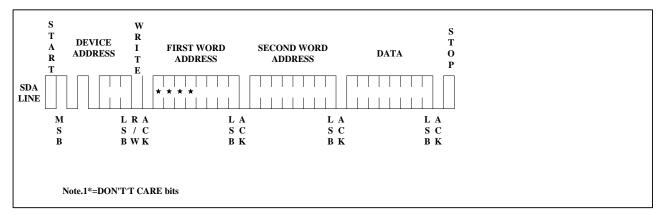


Figure 6. Byte Write

B15	B14	B13	B12	B11	B10	B9	B8
-----	-----	-----	-----	-----	-----	-----------	-----------

Table 3. FIRST WORD ADDRESS

B7	B6	B5	B4	B 3	B2	B1	BO	
----	-----------	----	-----------	------------	----	----	----	--

Table 4. SECOND WORD ADDRESS

PAGE WRITE: The Page Write mode allows up to 32 bytes to be written in a single Write cycle. A page write is initiated the same as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to 31 more data words. The EEPROM will respond with a "0" after each data word received. The microcontroller must terminate the page write sequence with a stop condition.

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The data word address lower five bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than 32 data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten (see **Figure 7**).

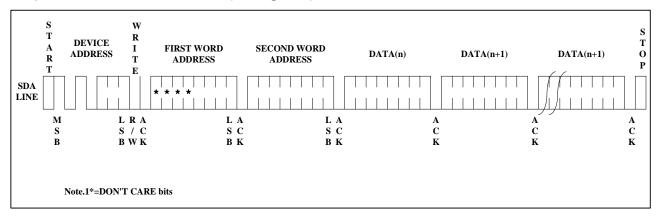


Figure 7. Page Write

ACKNOWLEDGE POLLING: Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a "0", allowing the read or write sequence to continue.



Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to "1". There are three read operations: current address read, random address read and sequential read.

CURRENT ADDRESS READ: The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page. Once the device address with the read/write select bit set to "1" is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input "0" but does generate a following stop condition (see **Figure 8**).

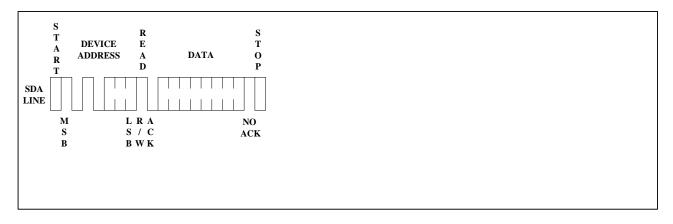


Figure 8. Current Address Read

RANDOM READ: A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a "0" but does generate a following stop condition (see **Figure 9**)

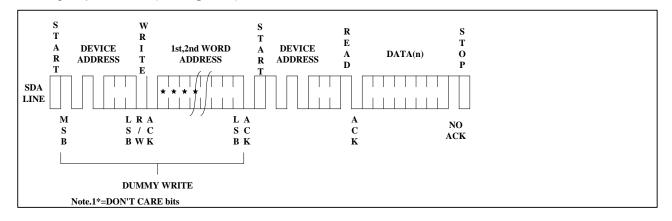
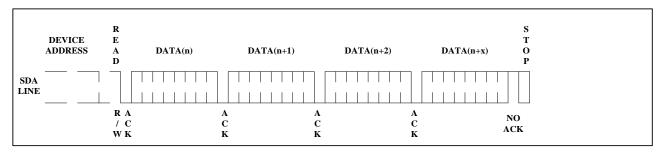


Figure 9. Random Read

SEQUENTIAL READ: Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a "0" but does generate a following stop condition (see **Figure 10**).

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Electrical Characteristics

Absolute Maximum Stress Ratings:

	DC Supply Voltage
٠	Operating Ambient Temperature
	Storage Temperature65°C to +150°C Electrostatic pulse (Human Body model)

Comments:

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to this device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied or intended. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

DC Electrical Characteristics

Applicable over recommended operating range from (unless otherwise noted):

BL24C32F	TA =-40	0°C to +85	۶°C	VCC =	+1.7V to +	⊦5.5V@4	00kHz
BL24C32FE1	TA =-40	0°C to +10	05℃	VCC =	+2.5V to +		
BL24C32FE0	TA =-40	0°C to +12	25℃	CL=100) pF		
Parameter		Symbol	Min	Тур	Max	Unit	Condition
Supply Current VCC=5.0V		Icc1	-	0.14	0.3	mA	READ at 400KHZ
Supply Current VCC=5.0V		Icc2	-	0.28	0.5	mA	WRITE at 400KHZ
Supply Current VCC=5.0V		SB1	-	0.03	0.5	μA	VIN=Vcc or Vss
Input Leakage Current		IL1	-	0.10	1.0	μA	VIN=Vcc or Vss
Output Leakage Current		Ilo	-	0.05	1.0	μA	Vout=Vcc or Vss
Input Low Level		VIL1	-0.3	-	Vcc×0.3	V	Vcc=1.7V to 5.5V
Input High Level		VIH1	Vcc×0.7	-	Vcc+0.3	V	Vcc=1.7V to 5.5V
Output Low Level VCC=1.	7V	Vol1	-	-	0.2	V	lo∟=0.15mA
Output Low Level VCC=5.	0V	Vol2	-	-	0.4	V	lo∟=3.0mA

Table 5

Pin Capacitance

Applicable over recommended operating range from TA = 25°C, f = 1.0 MHz, VCC = +1.7V

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Input/Output Capacitance(SDA)	Cı/o	-	-	8	pF	Vio=0V
Input Capacitance(A0,A1,A2,SCL)	CIN	-	-	6	pF	VIN=0V

Table 6

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AC Electrical Characteristics

Applicable over recommended operating range from (unless otherwise noted):

BL24C32F	TA =-40°C	to +85℃		VC	CC = +1	.7V to	+5.5V@	2400kH	7	
BL24C32FE1	TA =-40°C	to +105°C		VC	CC = +2	2.5V to			-	
BL24C32FE0	TA =-40°C	to +125℃		CL	_=100 p	θF				
Deremeter		Cumbol	1	.7V	′≤Vcc <	2.5V	2.5V	′≤Vcc ≺	5.5V	Linito
Parameter		Symbol	Μ	in	Тур	Max	Min	Тур	Max	Units
Clock Frequency,SCL		fsc∟	-	•	-	400	-	-	1000	kHz
Clock Pulse Width Low		tLOW	1.	3	-	-	0.5	-	-	μs
Clock Pulse Width High		t HIGH	0.	6	-	-	0.26	-	-	μs
Noise Suppression Time		tı	-		-	50	-	-	50	ns
Clock Low to Data Out Val	id	t AA	-		-	0.9	-	-	0.45	μs
Time the bus must be free new transmission can star		tBUF	1.	3	-	-	0.5	-	-	μs
Start Hold Time		t hd:sta	0.	6	-	-	0.25	-	-	μs
Start Setup Time		t su:sta	0.	6	-	-	0.25	-	-	μs
Data In Hold Time		thd:dat	C)	-	-	0	-	-	μs
Data in Setup Time		tsu:dat	10	00	-	-	100	-	-	ns
Input Rise Time(1)		tr	-		-	0.3	-	-	0.12	μs
Input Fall Time(1)		t⊧	-		-	0.3	-	-	0.12	μs
Stop Setup Time		tsu:sto	0.	6	-	-	0.25	-	-	μs
Data Out Hold Time		tон	5	0	-	-	50	-	-	ns
Write Cycle Time		tw R	-		1.9	3	-	1.9	3	ms
5.0V,25°C,Byte Mode(1)		Endurance	11	M	-	-	1M	-	-	Write Cycle

Table 7

Notes:

1. This parameter is characterized and is not 100% tested.

2. AC measurement conditions:

RL (connects to VCC): 1.3K

Input pulse voltages: 0.3VCC to 0.7VCC

Input rise and fall time: 50ns

Input and output timing reference voltages: 0.5VCC

The value of RL should be concerned according to the actual loading on the user's system.



Bus Timing

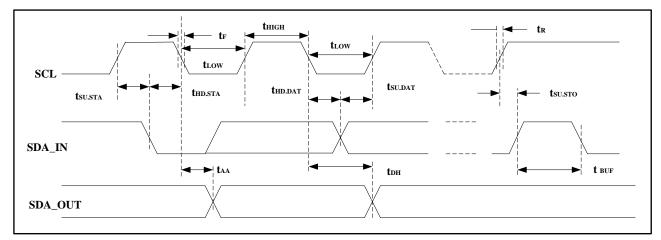


Figure 11. SCL: Serial Clock, SDA: Serial Data I/O

Write Cycle Timing

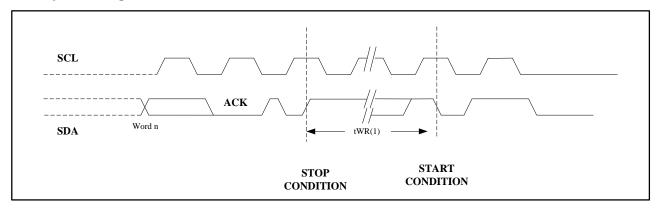


Figure 12. SCL: Serial Clock, SDA: Serial Data I/O

Notes:

The write cycle time tWR is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

Package Information

PDIP Outline Dimensions

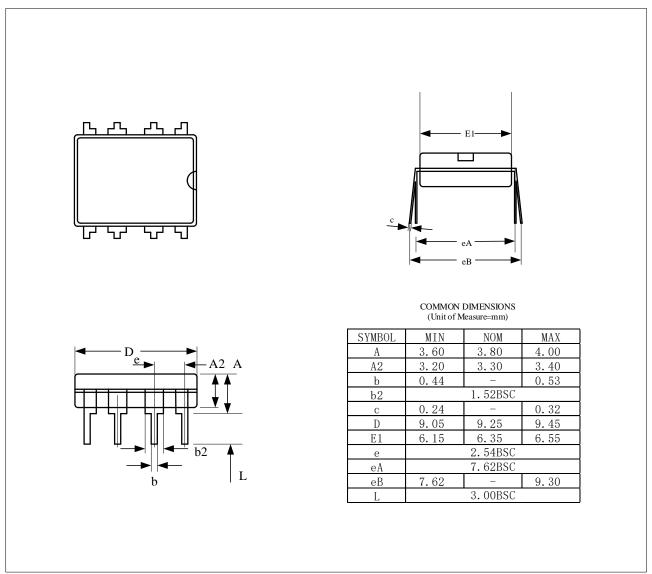


Figure 13



SOP

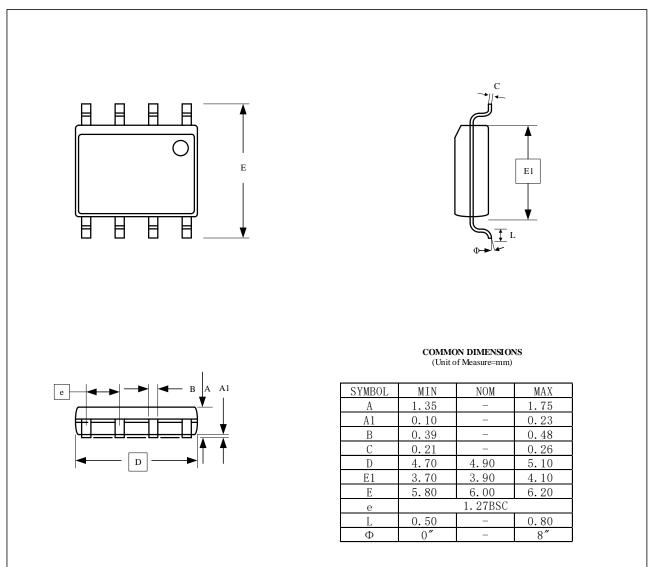


Figure 14

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TSSOP



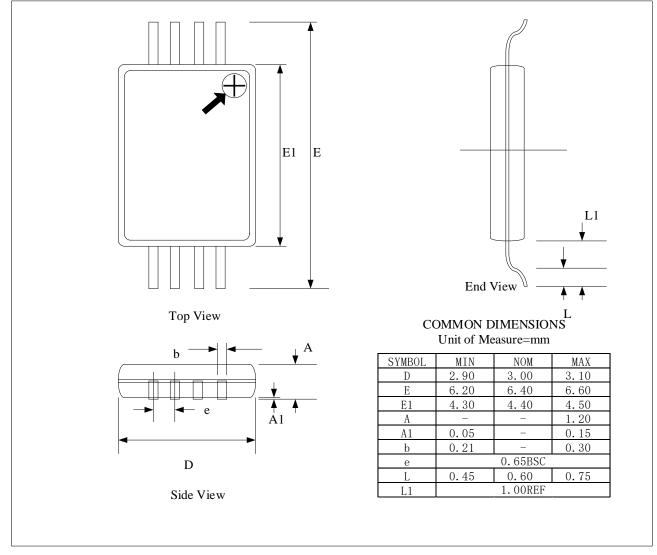


Figure 15

UDFN

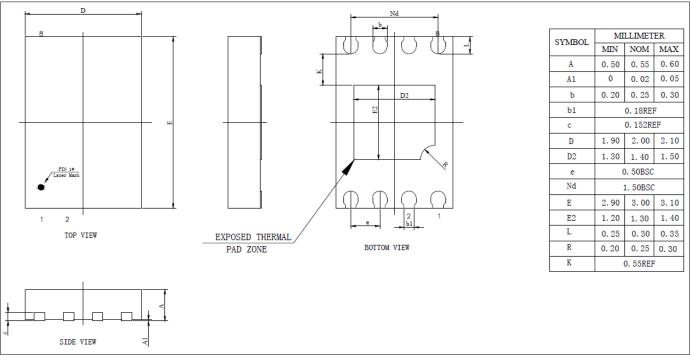


Figure 16

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2

TSOT23-5



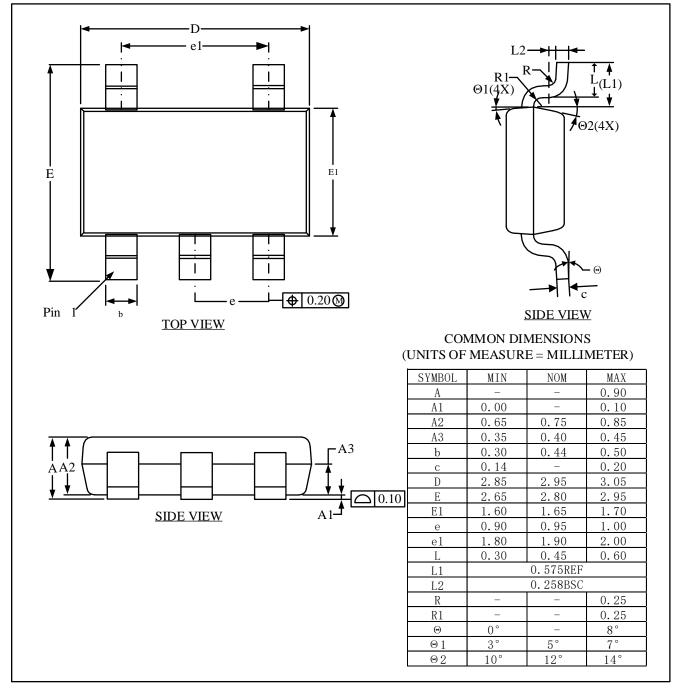
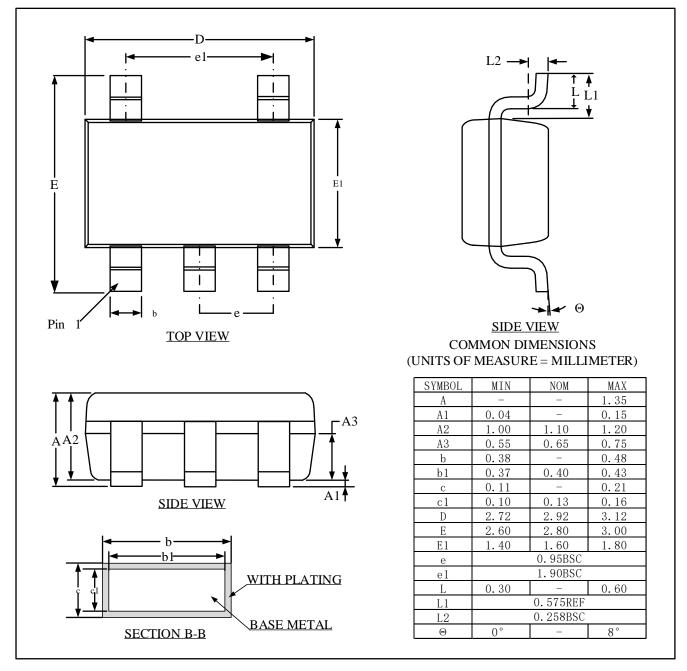


Figure 17

SOT23-5



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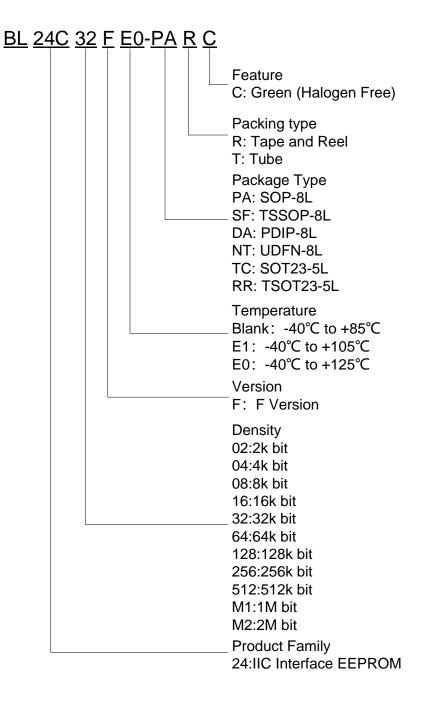


Marking Diagram

PDIP	
SOP	BL24C32F YYWW#ZZ SSSSSP O BL24C32F
	O SSSSSPE0
TSSOP	
	OBL24C32A SSSSS E0
UDFN	
	BL32A E0 YYWW O
SOT23-5/TSOT23-5	
	24C32F SSSSSP
YY	Year
WW	Week
ZZ SSSSS	assembly house
E0	Lot ID Blank: -40°C to +85°C
20	E1: -40° C to $+105^{\circ}$ C
	E0: -40°C to +125°C
P(TSOT23-5/SOT23-5)	P: -40℃ to +85℃ 1: -40℃ to +105℃

0: -40°C to +125°C

Ordering Information



Device	Package	Shipping (Qty/Packing)
BL24C32F	SOP8	2500/Tape &Reel
BL24C32F	TSSOP8L	3000/Tape &Reel
BL24C32F	UDFN	3000/Tape &Reel
BL24C32F	SOT23-5	3000/Tape &Reel
BL24C32F	TSOT23-5	3000/Tape &Reel

BL24C32F 32K bits (4,096×8) Belling Proprietary Information. Unauthorized Photocopy and Duplication Prohibited ©2018 Belling All Rights Reserved <u>www.belling.com.cn</u>

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Revision history

Version 1.00 BL24C32F	
Initial Version	
Version 1.01 BL24C32F	9/3/2018
Add TSOT23-5 Package information	
Modify Text and Structure of documents	
Version 1.02 BL24C32F	12/9/2018
Add SOT23-5 Package Information	
Update Operating Ambient Temperature Range Information	
Update Ordering information	
Version 1.03 BL24C32F	5/23/2022
Update Marking Diagram Information	

